B-Suffix Series CMOS Gates

The B Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- · All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range.
- Double Diode Protection on All Inputs Except: Triple Diode Protection on MC14011B and MC14081B
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices (Exceptions: MC14068B and MC14078B)







L SUFFIX CERAMIC CASE 632 P SUFFIX PLASTIC CASE 646 D SUFFIX SOIC CASE 751A

ORDERING INFORMATION

MC14XXXBCP Plastic
MC14XXXBCL Ceramic
MC14XXXBD SOIC

 $T_A = -55^{\circ}$ to 125°C for all packages.

MAXIMUM RATINGS* (Voltages Referenced to VSS)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage	- 0.5 to + 18.0	٧
V _{in} , V _{out}	Input or Output Voltage (DC or Transient)	-0.5 to $V_{DD} + 0.5$	V
l _{in} , l _{out}	Input or Output Current (DC or Transient), per Pin	± 10	mA
PD	Power Dissipation, per Package†	500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature (8–Second Soldering)	260	°C

^{*} Maximum Ratings are those values beyond which damage to the device may occur. †Temperature Derating:

Plastic "P and D/DW" Packages: – 7.0 mW/°C From 65°C To 125°C Ceramic "L" Packages: – 12 mW/°C From 100°C To 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}.$

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either VSS or VDD). Unused outputs must be left open.

MC14001B Quad 2-Input NOR Gate

MC14002B

Dual 4-Input NOR Gate

MC14011B

Quad 2-Input NAND Gate

MC14012B

Dual 4-Input NAND Gate

MC14023B

Triple 3-Input NAND Gate

MC14025B

Triple 3-Input NOR Gate

MC14068B

8-Input NAND Gate

MC14071B

Quad 2-Input OR Gate

MC14072B

Dual 4-Input OR Gate

MC14073B

Triple 3-Input AND Gate

MC14075B

Triple 3-Input OR Gate

MC14078B

8-Input NOR Gate

MC14081B

Quad 2-Input AND Gate

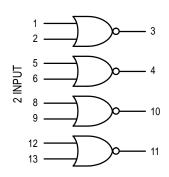
MC14082B

Dual 4-Input AND Gate

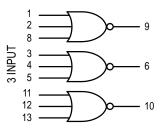
LOGIC DIAGRAMS

MC14001B Quad 2-Input NOR Gate

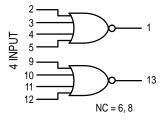
NOR



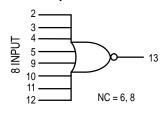
MC14025B Triple 3-Input NOR Gate



MC14002B Dual 4-Input NOR Gate

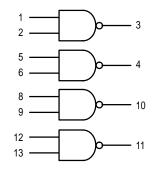


MC14078B 8-Input NOR Gate

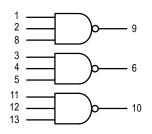


NAND

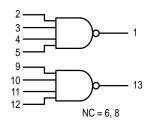
MC14011B Quad 2-Input NAND Gate



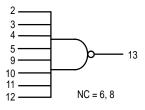
MC14023B
Triple 3-Input NAND Gate



MC14012B Dual 4-Input NAND Gate

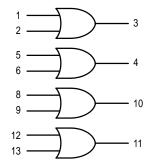


MC14068B 8-Input NAND Gate

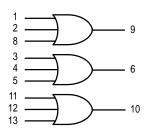


OR

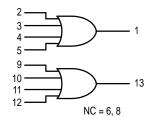
MC14071B Quad 2-Input OR Gate



MC14075B Triple 3–Input OR Gate

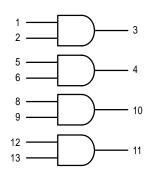


MC14072B Dual 4-Input OR Gate

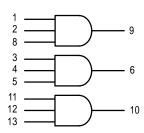


AND

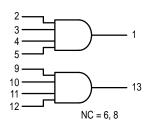
MC14081B Quad 2-Input AND Gate



MC14073B Triple 3-Input AND Gate

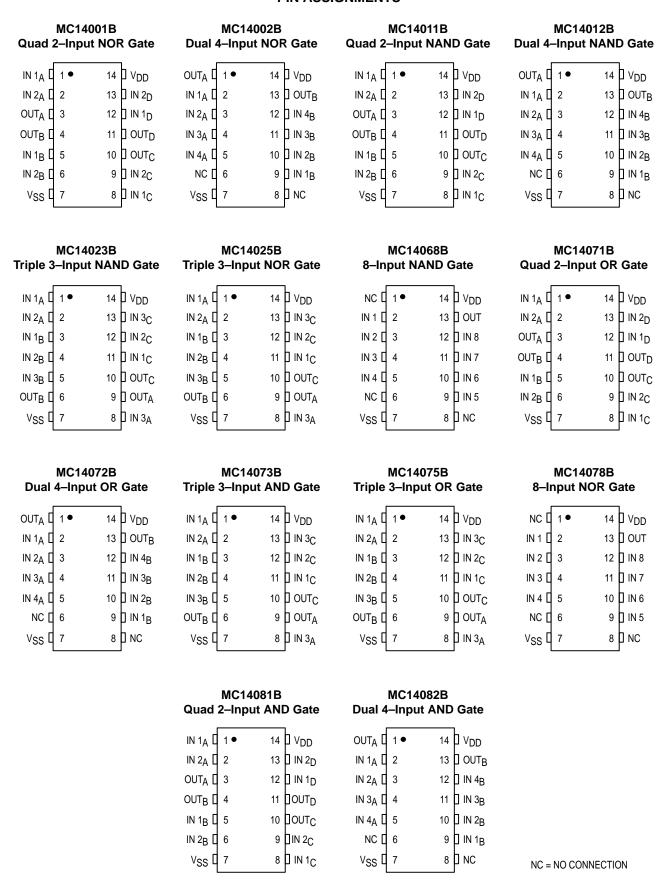


MC14082B Dual 4-Input AND Gate



 V_{DD} = PIN 14 V_{SS} = PIN 7 FOR ALL DEVICES

PIN ASSIGNMENTS



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

			V _{DD}	- 5	5°C		25°C		125	5°C	
Characteristic		Symbol	Vdc	Min	Max	Min	Тур#	Max	Min	Max	Unit
Output Voltage V _{in} = V _{DD} or 0	"0" Level	VOL	5.0 10 15	_ _ _	0.05 0.05 0.05	_ _ _	0 0 0	0.05 0.05 0.05	_ _ _	0.05 0.05 0.05	Vdc
V _{in} = 0 or V _{DD}	"1" Level	VOH	5.0 10 15	4.95 9.95 14.95	_ _ _	4.95 9.95 14.95	5.0 10 15	_ _ _	4.95 9.95 14.95	_ _ _	Vdc
Input Voltage (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc)	"0" Level	V _I L	5.0 10 15		1.5 3.0 4.0		2.25 4.50 6.75	1.5 3.0 4.0	_ _ _	1.5 3.0 4.0	Vdc
$(V_O = 0.5 \text{ or } 4.5 \text{ Vdc})$ $(V_O = 1.0 \text{ or } 9.0 \text{ Vdc})$ $(V_O = 1.5 \text{ or } 13.5 \text{ Vdc})$	"1" Level	VIH	5.0 10 15	3.5 7.0 11	_ _ _	3.5 7.0 11	2.75 5.50 8.25	_ _ _	3.5 7.0 11	_ _ _	Vdc
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	Source	ЮН	5.0 5.0 10 15	- 3.0 - 0.64 - 1.6 - 4.2		- 2.4 - 0.51 - 1.3 - 3.4	- 4.2 - 0.88 - 2.25 - 8.8		- 1.7 - 0.36 - 0.9 - 2.4		mAdc
$(V_{OL} = 0.4 \text{ Vdc})$ $(V_{OL} = 0.5 \text{ Vdc})$ $(V_{OL} = 1.5 \text{ Vdc})$	Sink	lOL	5.0 10 15	0.64 1.6 4.2	_ _	0.51 1.3 3.4	0.88 2.25 8.8		0.36 0.9 2.4		mAdc
Input Current		l _{in}	15	_	± 0.1	_	±0.00001	± 0.1	_	± 1.0	μAdc
Input Capacitance (Vin = 0)		C _{in}	_	_	_	_	5.0	7.5	_	_	pF
Quiescent Current (Per Package)		IDD	5.0 10 15	_ _ _	0.25 0.5 1.0	_ _ _	0.0005 0.0010 0.0015	0.25 0.5 1.0	_ _ _	7.5 15 30	μAdc
Total Supply Current**† (Dynamic plus Quiesce Per Gate, C _L = 50 pF)	nt,	lΤ	5.0 10 15			$I_{T} = (0.$	3 μΑ/kHz) f - 6 μΑ/kHz) f - 9 μΑ/kHz) f -	- I _{DD} /N			μAdc

[#]Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μ A (per package), C_L in pF, $V = (V_{DD} - V_{SS})$ in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

^{**}The formulas given are for the typical characteristics only at 25 $^{\circ}\text{C}.$

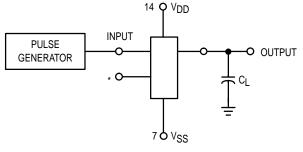
[†]To calculate total supply current at loads other than 50 pF:

B-SERIES GATE SWITCHING TIMES

SWITCHING CHARACTERISTICS* ($C_L = 50 \text{ pF}, T_A = 25^{\circ}C$)

tTLH					
	5.0 10 15	_ 	100 50 40	200 100 80	ns
[†] THL	5.0 10 15		100 50 40	200 100 80	ns
PLH, [†] PHL	5.0 10 15 5.0 10 15 5.0		125 50 40 160 65 50 200 80	250 100 80 300 130 100 350 150	ns
- iP		5.0 10 15 PLH, [†] PHL 5.0 10 15 5.0 10 15 5.0	5.0 — 15 — 15 — 15 — 15 — 15 — 15 — 15 — 1	15 — 40 TTHL 5.0 — 100 10 — 50 15 — 40 PLH, tPHL 5.0 — 125 10 — 50 15 — 40 5.0 — 160 10 — 65 15 — 50 15 — 200 10 — 80	15 — 40 80 TTHL 5.0 — 100 200 10 — 50 100 15 — 40 80 PLH, tPHL 5.0 — 125 250 10 — 50 100 15 — 40 80 5.0 — 160 300 10 — 65 130 15 — 50 100 5.0 — 200 350 10 — 80 150

^{*}The formulas given are for the typical characteristics only at 25°C.



 $^{^{\}star}$ All unused inputs of AND, NAND gates must be connected to V_{DD}. All unused inputs of OR, NOR gates must be connected to V_{SS}.

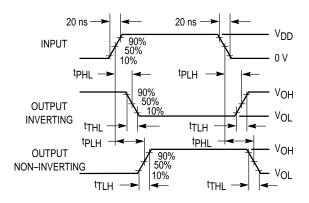
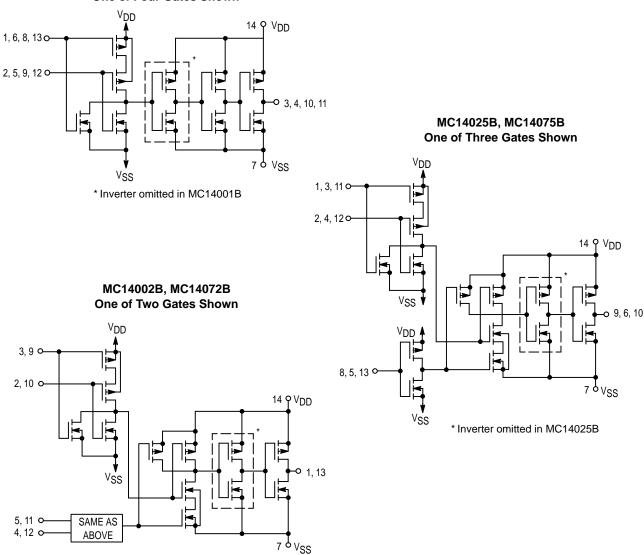


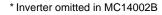
Figure 1. Switching Time Test Circuit and Waveforms

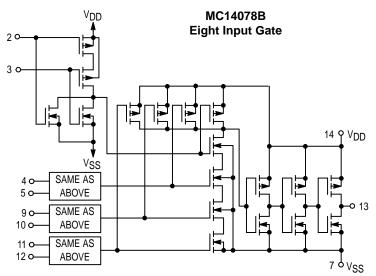
[#]Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

CIRCUIT SCHEMATIC NOR, OR GATES

MC14001B, MC14071B One of Four Gates Shown







CIRCUIT SCHEMATIC NAND, AND GATES

MC14011B, MC14081B One of Four Gates Shown 14 9 V_{DD} MC14023B, MC14073B O 3, 4, 10, 11 One of Three Gates Shown 2, 5, 9, 12 0 V_{DD} 1, 6, 8, 13 0 * Inverter omitted in MC14011B 2, 4, 12 0 14 o V_{DD} 1, 3, 11 🗢 Vss V_{DD} 9, 6, 10 MC14012B, MC14082B 8, 5, 130 One of Two Gates Shown Λ^{DD} Vss * Inverter omitted in MC14023B 14 9 V_{DD} MC14068B **Eight Input Gate** 2, 10 o- V_{DD} 3,90 Vss 1, 13 4, 12 0-SAME AS 5, 11 0-ABOVE V_{DD} 7 6 VSS * Inverter omitted in MC14012B Vss SAME AS ABOVE 14 9 V_{DD} ٧ss V_{DD} 4 SAME AS 90-10 O-ABOVE 11 0-SAME AS ABOVE 74 VSS

 V_{SS}

TYPICAL B-SERIES GATE CHARACTERISTICS

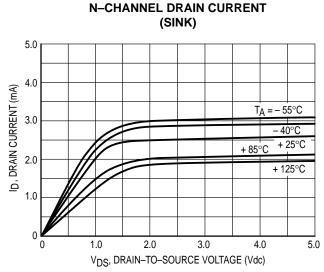


Figure 2. $V_{GS} = 5.0 \text{ Vdc}$

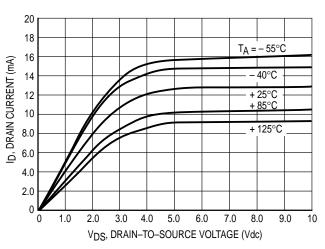


Figure 4. VGS = 10 Vdc

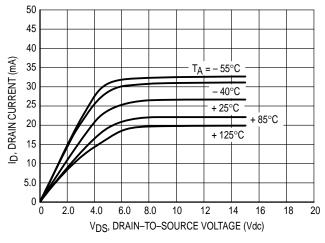


Figure 6. VGS = 15 Vdc

(SOURCE) - 10 $T_A = -55^{\circ}C$

P-CHANNEL DRAIN CURRENT

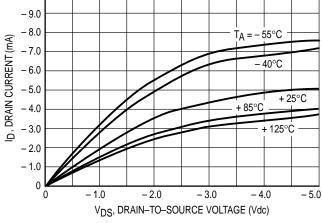


Figure 3. $V_{GS} = -5.0 \text{ Vdc}$

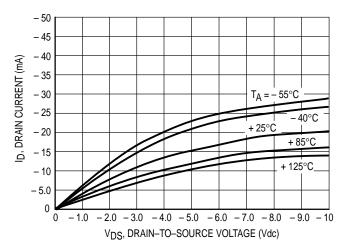


Figure 5. $V_{GS} = -10 \text{ Vdc}$

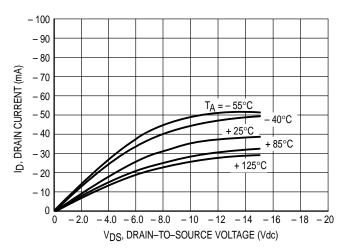


Figure 7. $V_{GS} = -15 \text{ Vdc}$

These typical curves are not guarantees, but are design aids. Caution: The maximum rating for output current is 10 mA per pin.

TYPICAL B-SERIES GATE CHARACTERISTICS (cont'd)

VOLTAGE TRANSFER CHARACTERISTICS

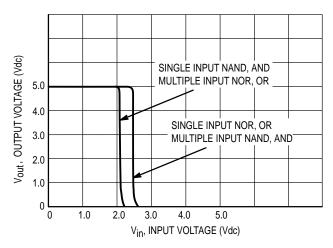


Figure 8. V_{DD} = 5.0 Vdc

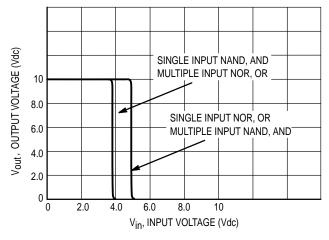


Figure 9. V_{DD} = 10 Vdc

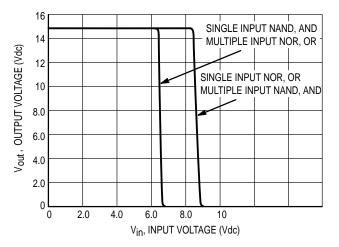


Figure 10. V_{DD} = 15 Vdc

DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal "1" or "0" input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the "1" and "0" levels =

1.0 V with a 5.0 V supply

2.0 V with a 10.0 V supply

2.5 V with a 15.0 V supply

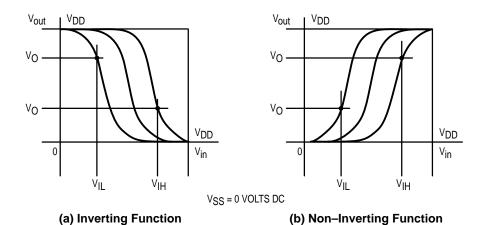
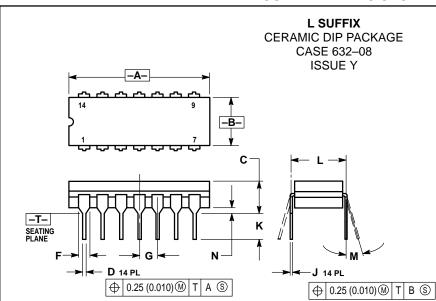


Figure 11. DC Noise Immunity

OUTLINE DIMENSIONS



- IOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: INCH.

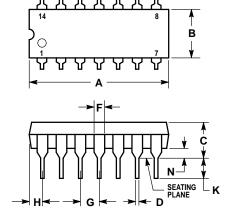
 3. DIMENSION I TO CENTER OF LEAD WHEN FORMED PARALLEL.

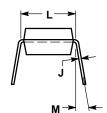
 4. DIMENSION F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.750	0.785	19.05	19.94	
В	0.245	0.280	6.23	7.11	
C	0.155	0.200	3.94	5.08	
ם	0.015	0.020	0.39	0.50	
F	0.055	0.065	1.40	1.65	
G	0.100	BSC	2.54 BSC		
7	0.008	0.015	0.21	0.38	
K	0.125	0.170	3.18	4.31	
۲	0.300	BSC	7.62 BSC		
M	0°	15°	0 °	15°	
N	0.020	0.040	0.51	1.01	

P SUFFIX

PLASTIC DIP PACKAGE CASE 646-06 ISSUE L





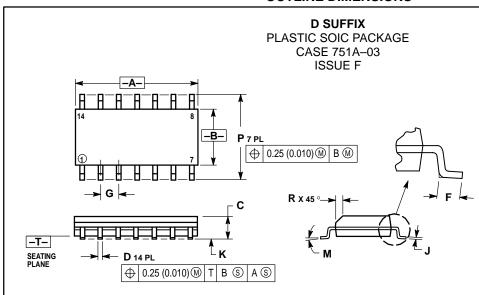
- NOTES:

 1. LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.

 2. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
- DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.715	0.770	18.16	19.56	
В	0.240	0.260	6.10	6.60	
С	0.145	0.185	3.69	4.69	
D	0.015	0.021	0.38	0.53	
F	0.040	0.070	1.02	1.78	
G	0.100	BSC	2.54 BSC		
Н	0.052	0.095	1.32	2.41	
J	0.008	0.015	0.20	0.38	
K	0.115	0.135	2.92	3.43	
L	0.300 BSC		7.62 BSC		
M	0°	10°	0°	10°	
N	0.015	0.039	0.39	1.01	

OUTLINE DIMENSIONS



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS A AND B DO NOT INCLUDE
 MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	METERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050	BSC	
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

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